

BCM61B

NPN/NPN matched double transistor

Rev. 02 — 28 August 2009

Product data sheet

1. Product profile

1.1 General description

NPN/NPN matched double transistor in a SOT143B small Surface-Mounted Device (SMD) plastic package. Matched version of BCV61.

PNP/PNP equivalent: BCM62B

1.2 Features

Current gain matching

1.3 Applications

- Current mirror
- Differential amplifier

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor TR1					
V_{CEO}	collector-emitter voltage	open base	-	-	45	V
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V};$ $I_C = 2 \text{ mA}$	200	290	450	
Per transis	tor					
I _C	collector current		-	-	100	mA
Per device						
I _{C1} /I _{E2}	current matching	$V_{CE1} = 5 \text{ V};$ $I_{E2} = -0.5 \text{ mA};$ $T_{amb} \le 25 \text{ °C}$	[<u>1</u>] 0.92	1.02	1.12	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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2. Pinning information

Table 2. Pinning

Table 2.	Pinning		
Pin	Description	Simplified outline	Symbol
1	collector TR2, base TR1 and TR2		
2	collector TR1	4 3	4 3
3	emitter TR1		TR2 TR1
4	emitter TR2	1 2	
			1 2

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BCM61B	-	plastic surface-mounted package; 4 leads	SOT143B

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
BCM61B	*AC

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor TR1				
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	45	V
Per transis	stor				
V_{EBS}	emitter-base voltage	$V_{CB} = 0 V$	-	6	V
I _C	collector current		-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1] -	220	mW
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1] -	390	mW
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	568	K/W
Per devic	e					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	321	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transis	stor TR1						
I _{CBO}	collector-base cut-off current	$V_{CB} = 30 \text{ V};$ $I_E = 0 \text{ A}$		-	-	15	nA
		$V_{CB} = 30 \text{ V};$ $I_{E} = 0 \text{ A};$ $T_{j} = 150 \text{ °C}$		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$		-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V};$ $I_C = 10 \mu\text{A}$		-	250	-	
		$V_{CE} = 5 \text{ V};$ $I_{C} = 100 \mu\text{A}$		100	-	-	
		$V_{CE} = 5 \text{ V};$ $I_C = 2 \text{ mA}$		200	290	450	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA};$ $I_B = 0.5 \text{ mA}$		-	50	200	mV
		$I_C = 100 \text{ mA};$ $I_B = 5 \text{ mA}$		-	200	400	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = 10 \text{ mA};$ $I_B = 0.5 \text{ mA}$	<u>[1]</u>	-	760	-	mV
		$I_C = 100 \text{ mA};$ $I_B = 5 \text{ mA}$	<u>[1]</u>	-	910	-	mV
V_{BE}	base-emitter voltage	$V_{CE} = 5 \text{ V};$ $I_C = 2 \text{ mA}$	[2]	610	660	710	mV
		$V_{CE} = 5 \text{ V};$ $I_C = 10 \text{ mA}$	[2]	-	-	770	mV
C _c	collector capacitance	$V_{CB} = 10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	-	1.5	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V};$ $I_C = i_c = 0 \text{ A};$ $f = 1 \text{ MHz}$		-	11	-	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V};$ $I_{C} = 10 \text{ mA};$ $f = 100 \text{ MHz}$		100	250	-	MHz
NF I	noise figure	$V_{CE} = 5 \text{ V};$ $I_{C} = 0.2 \text{ mA};$ $R_{S} = 2 \text{ k}\Omega;$ $f = 10 \text{ Hz to}$ 15.7 kHz		-	2.8	-	dB
		$V_{CE} = 5 \text{ V};$ $I_{C} = 0.2 \text{ mA};$ $R_{S} = 2 \text{ k}\Omega;$ $f = 1 \text{ kHz};$ $B = 200 \text{ Hz}$		-	3.3	-	dB

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Table 7. Characteristics ...continued $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified

	-					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor TR2					
V _{EBS}	emitter-base voltage	$V_{CB} = 0 \text{ V};$ $I_E = -250 \text{ mA}$	-	-	-1.8	V
		$V_{CB} = 0 \text{ V};$ $I_E = -10 \mu\text{A}$	-400	-	-	mV
Per device)					
I _{C1} /I _{E2} c	current matching	$V_{CE1} = 5 \text{ V};$ $I_{E2} = -0.5 \text{ mA};$ $T_{amb} \le 25 \text{ °C}$	[<u>3</u>] 0.92	1.02	1.12	
		$V_{CE1} = 5 \text{ V};$ $I_{E2} = -0.5 \text{ mA};$ $T_{amb} \le 150 \text{ °C}$	[<u>3]</u> 0.93	-	1.13	
		$V_{CE1} = 3 \text{ V};$ $I_{E2} = -0.5 \text{ mA};$ $T_{amb} \le 25 \text{ °C}$	[<u>3</u>] 0.91	1.01	1.11	
		$V_{CE1} = 1 \text{ V};$ $I_{E2} = -0.5 \text{ mA};$ $T_{amb} \le 25 \text{ °C}$	[3] 0.9	1	1.1	

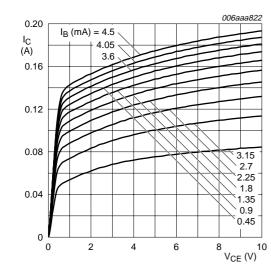
^[1] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

^[2] V_{BE} decreases by about 2 mV/K with increasing temperature.

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

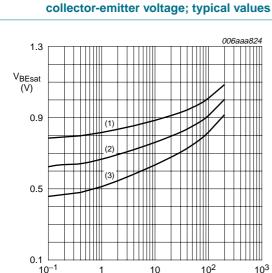
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T_{amb} = 25 °C

Collector current as a function of Fig 1.



 $I_{\rm C}/I_{\rm B}=20$

(1) $T_{amb} = -55 \,^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

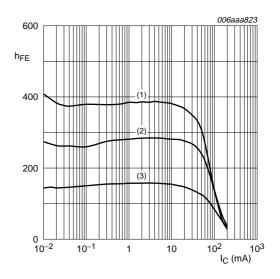
Base-emitter saturation voltage as a function Fig 3. of collector current; typical values

10

10²

I_C (mA)

10³



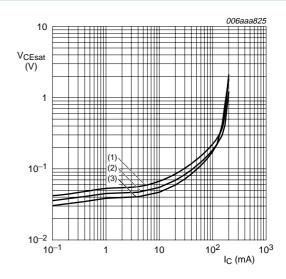
 $V_{CE} = 5 V$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55$ °C

DC current gain as a function of collector Fig 2. current; typical values



 $I_{\rm C}/I_{\rm B}=20$

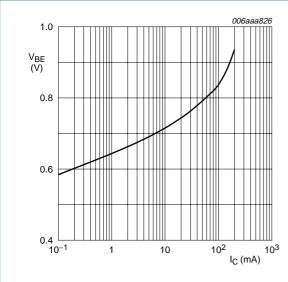
(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55$ °C

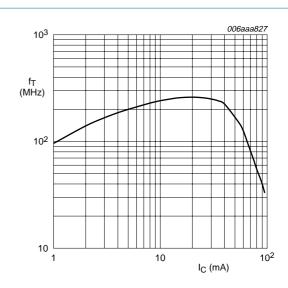
Collector-emitter saturation voltage as a Fig 4. function of collector current; typical values

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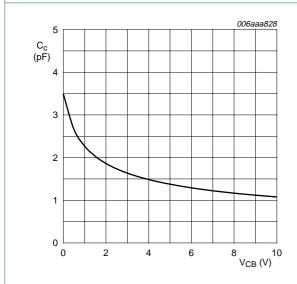
 $V_{CE} = 5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$

Fig 5. Base-emitter voltage as a function of collector current; typical values



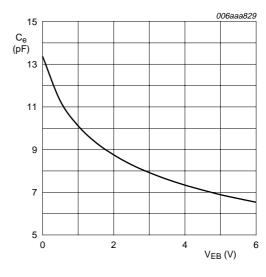
 V_{CE} = 5 V; T_{amb} = 25 °C

Fig 6. Transition frequency as a function of collector current; typical values



collector-base voltage; typical values

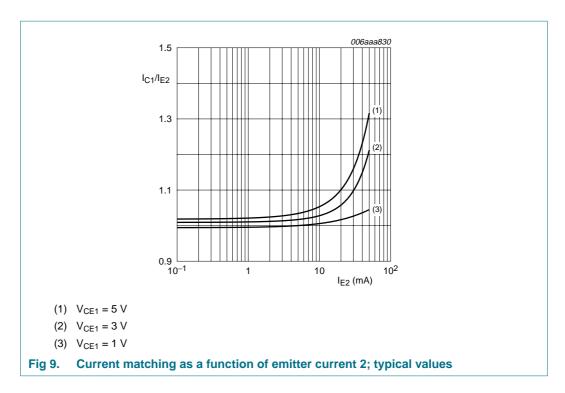
 $f = 1 \text{ MHz; } T_{amb} = 25 \text{ °C}$ Fig 7. Collector capacitance as a function of



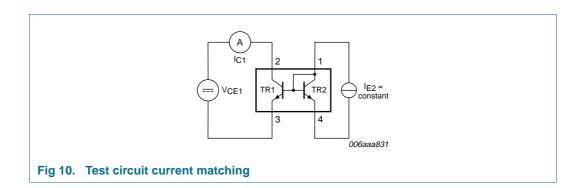
 $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$

Fig 8. Emitter capacitance as a function of emitter-base voltage; typical values

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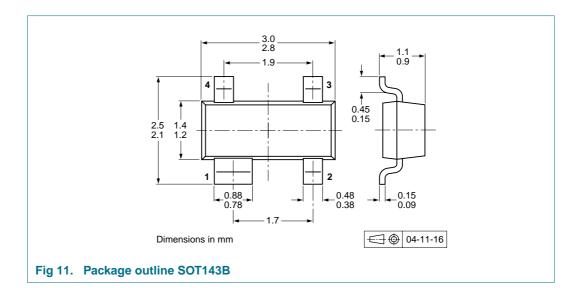


8. Test information



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9. Package outline

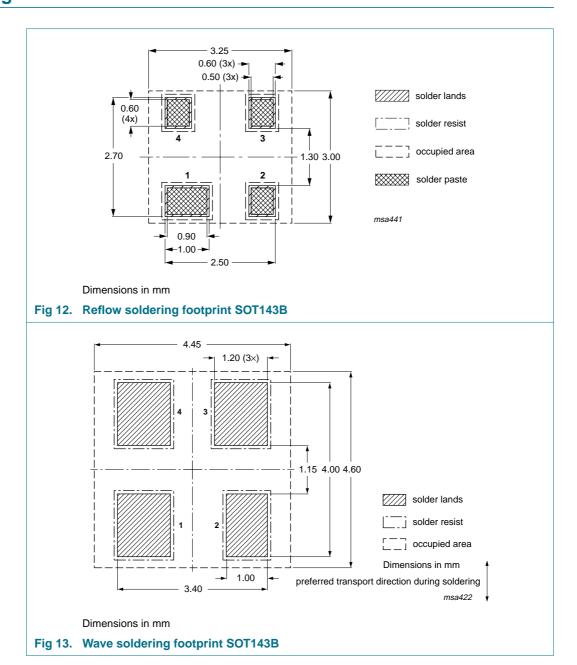


10. Packing information

Please refer to packing information on www.nexperia.com.

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11. Soldering



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12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BCM61B_2	20090828	Product data sheet	-	BCM61B_1
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. Figure 13 "Wave soldering footprint SOT143B": updated 			
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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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